

100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

52 A

Features

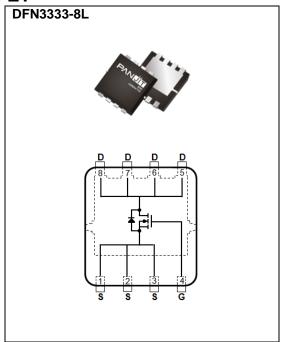
- RDS(ON), VGS@10V, ID@10A<11.3m Ω
- RDS(ON), VGS@4.5V, ID@6A<17m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current(Note 3)	Tc=25°C		52		
	T _C =100°C	l _D	36	Α	
Pulsed Drain Current(Note 1)	Tc=25°C	I _{DM}	208		
Power Dissipation	Tc=25°C	D-	60	W	
	T _C =100°C	Po	30		
Continuous Drain Current(Note 4)	T _A =25°C	I _D	10.5	А	
	T _A =70°C		8.8		
Power Dissipation	T _A =25°C	Po	2.5	W	
	T _A =70°C		1.8		
Single Pulse Avalanche Current(Note 5)		las	17.5	Α	
Single Pulse Avalanche Energy ^(Note 5)		Eas	25	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	2.5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	60		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	SS V _{GS} =0V, I _D =250uA 100		-	-	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.5	1.9	3	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A	-	9.1	11.3	mΩ	
		V _{GS} =4.5V, I _D =6A	-	13	17		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
Dynamic ^(Note 6)	•		•		•		
Total Gate Charge	Qg	V _{DS} =50V, I _D =10A,	-	35	-	nC	
Gate-Source Charge	Qgs		-	7	-		
Gate-Drain Charge	Q _{gd}	V _{GS} =10V ^(Note 2,3)	-	10	-		
Input Capacitance	Ciss	V _{DS} =50V, V _{GS} =0V,	-	1459	-	pF	
Output Capacitance	Coss		-	272	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	15	-		
Gate resistance	Rg	f=1MHz	-	0.84	-	Ω	
Turn-On Delay Time	td _(on)	V _{DS} =50V, I _D =10A,	-	8	-		
Turn-On Rise Time	tr		-	20	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=3\Omega$	-	27	-	ns	
Turn-Off Fall Time	tf	- (Note 2,3)	-	21	-		
Drain-Source Diode	•	1		•		•	
Diode Forward Current	Is	T 0500	-	-	52	Α	
Pulsed Diode Forward Current	I _{SM}	T _C =25°C	-	-	208		
Diode Forward Voltage	V_{SD}	Is=20A, V _G s=0V	-	0.85	1.3	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	39	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us ^(Note 2,3)	-	31	-	nC	

NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an $R_{\theta JC}=2.5^{\circ}C/W$.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. Eas is calculated based on the condition of L=1mH, Ias=7A, VDD=30V, VGS=10V. 100% test at L=0.1mH, Ias=17.5A in production.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

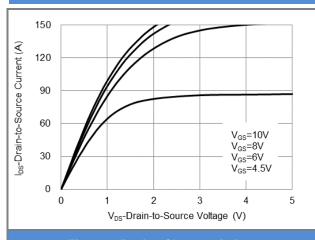


Fig.1 On-Region Characteristics

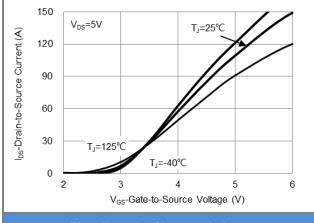


Fig.2 Transfer Characteristics

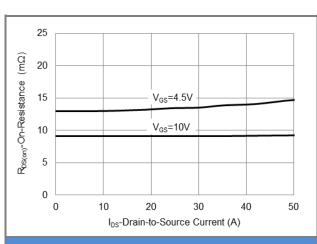


Fig.3 On-Resistance vs. Drain Current

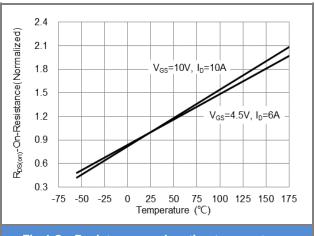


Fig.4 On-Resistance vs. Junction temperature

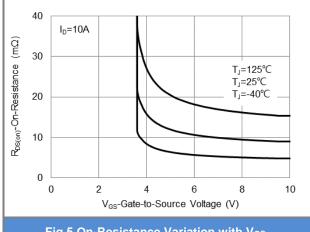


Fig.5 On-Resistance Variation with V_{GS}

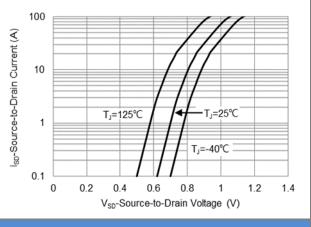


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

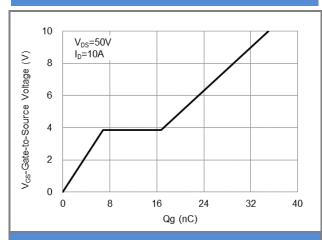


Fig.7 Gate-Charge Characteristics

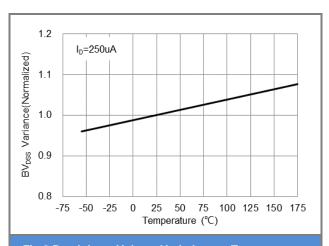


Fig.8 Breakdown Voltage Variation vs. Temperature

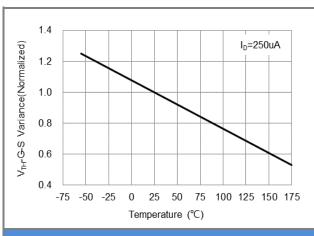


Fig.9 Threshold Voltage Variation with Temperature

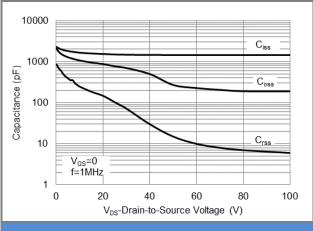
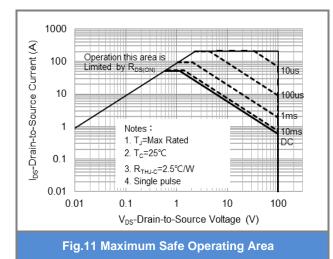


Fig.10 Capacitance vs. Drain-Source Voltage



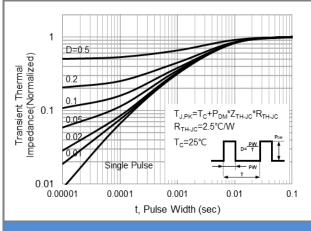


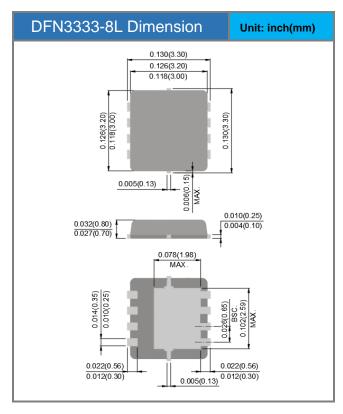
Fig.12 Normalized Transient Thermal Impedance

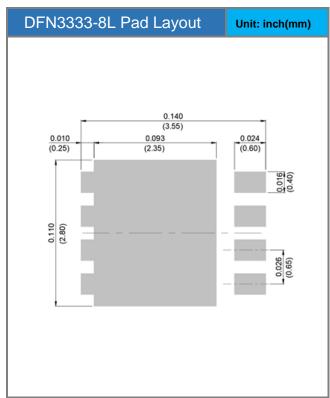


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ4574AP-AU	DFN3333-8L	5K pcs / 13" reel	574A	

Packaging Information & Mounting Pad Layout







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